

TVS Diode

Transient Voltage Suppressor Diodes

ESD5V3S1B-02LS

Bi-directional Symmetrical Medium Capacitance ESD / Transient Protection Diode

ESD5V3S1B-02LS

Data Sheet

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Final

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Revision History

Page or Item	Subjects (major changes since previous revision)
Revision 1.0, 2011-04-08	

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1 Bi-directional Symmetrical Medium Capacitance ESD / Transient Protection Diode

1.1 Features

- ESD / transient protection of signal lines in low voltage applications according to:
 - IEC61000-4-2 (ESD): ± 20 kV (contact)
 - IEC61000-4-4 (EFT): 40 A / 2 kV (5/50 ns)
 - IEC61000-4-5 (surge): 5 A (8/20 μ s)
- Bi-directional, symmetrical working voltage up to $V_{RWM} = \pm 5.3$ V
- Low clamping voltage, low dynamic resistance $R_{DYN} = 0.5 \Omega$ (typical)
- Smallest form factor: $0.62 \times 0.32 \times 0.31$ mm³
- Pb-free (RoHS compliant) and halogen free package



1.2 Application Examples

- Audio line protection
- Mobile communication, Consumer products (STB, MP3, DVD, DSC...)
- LCD displays, keypads, trackball protection, camera
- Notebooks and desktop computers, peripherals

2 Product Description

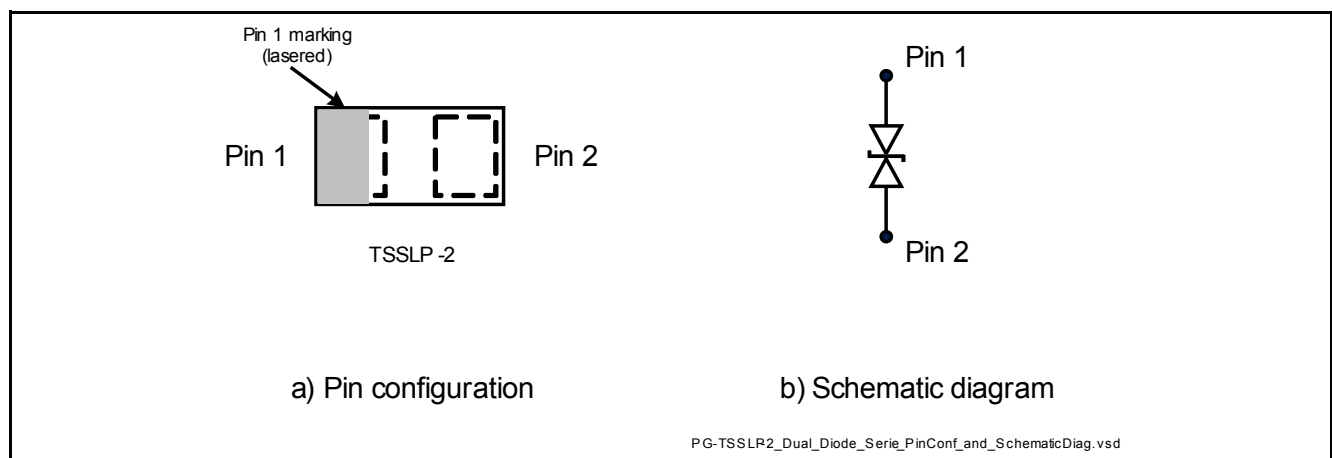


Figure 2-1 Pin Configuration and Schematic Diagram

Table 2-1 Ordering Information

Type	Package	Configuration	Marking code
ESD5V3S1B-02LS	PG-TSSLP-2-1	1 line, bi-directional	H

3 Characteristics

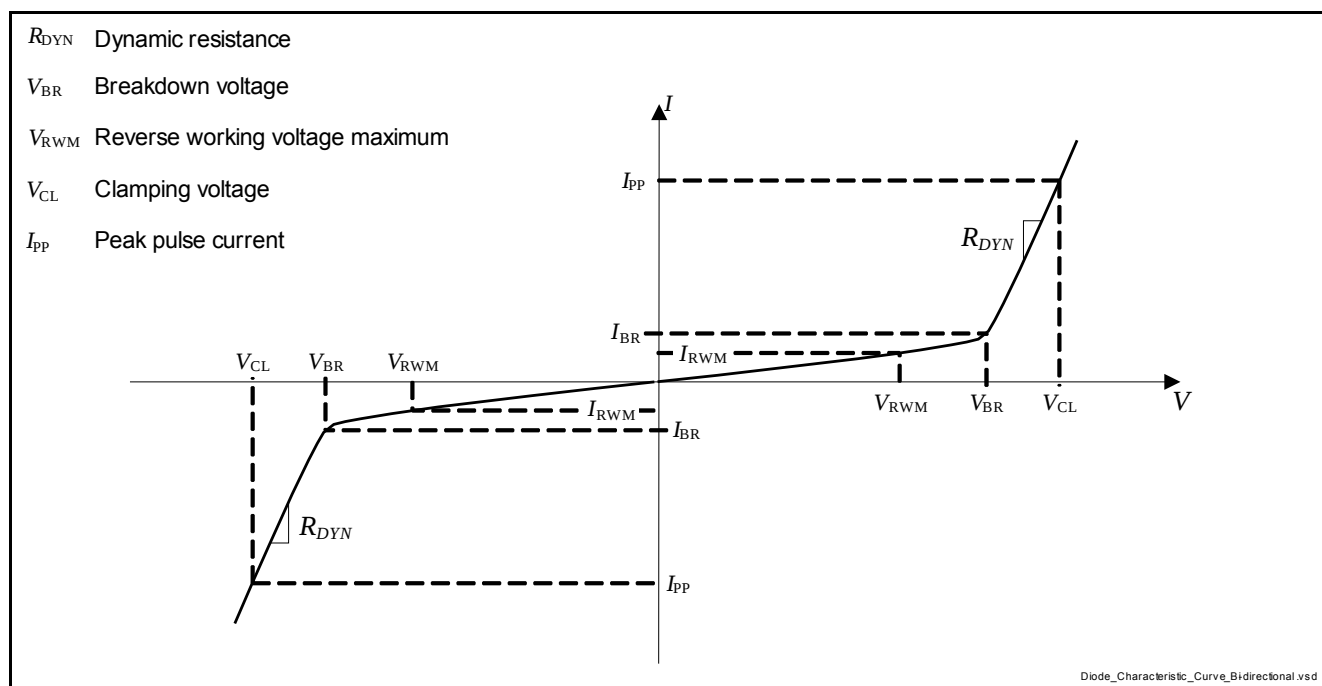
Table 3-1 Maximum Ratings at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
ESD contact discharge ¹⁾	V_{ESD}	–	–	20	kV
Peak pulse current ($t_p = 8/20\text{ }\mu\text{s}$) ²⁾	I_{PP}	–	–	5	A
Operating temperature range	T_{OP}	-40	–	125	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55	–	150	$^{\circ}\text{C}$

1) V_{ESD} according to IEC61000-4-2

2) I_{PP} according to IEC61000-4-5

3.1 Electrical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified


Figure 3-1 Definitions of electrical characteristics
Table 3-2 DC Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse working voltage	V_{RWM}	-5.3	–	5.3	V	
Breakdown voltage	V_{BR}	6	–	–	V	$I_{\text{R}} = 1\text{ mA}$
Reverse current	I_{R}	–	–	0.1	μA	$V_{\text{R}} = 3.3\text{ V}$

Table 3-3 RF Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

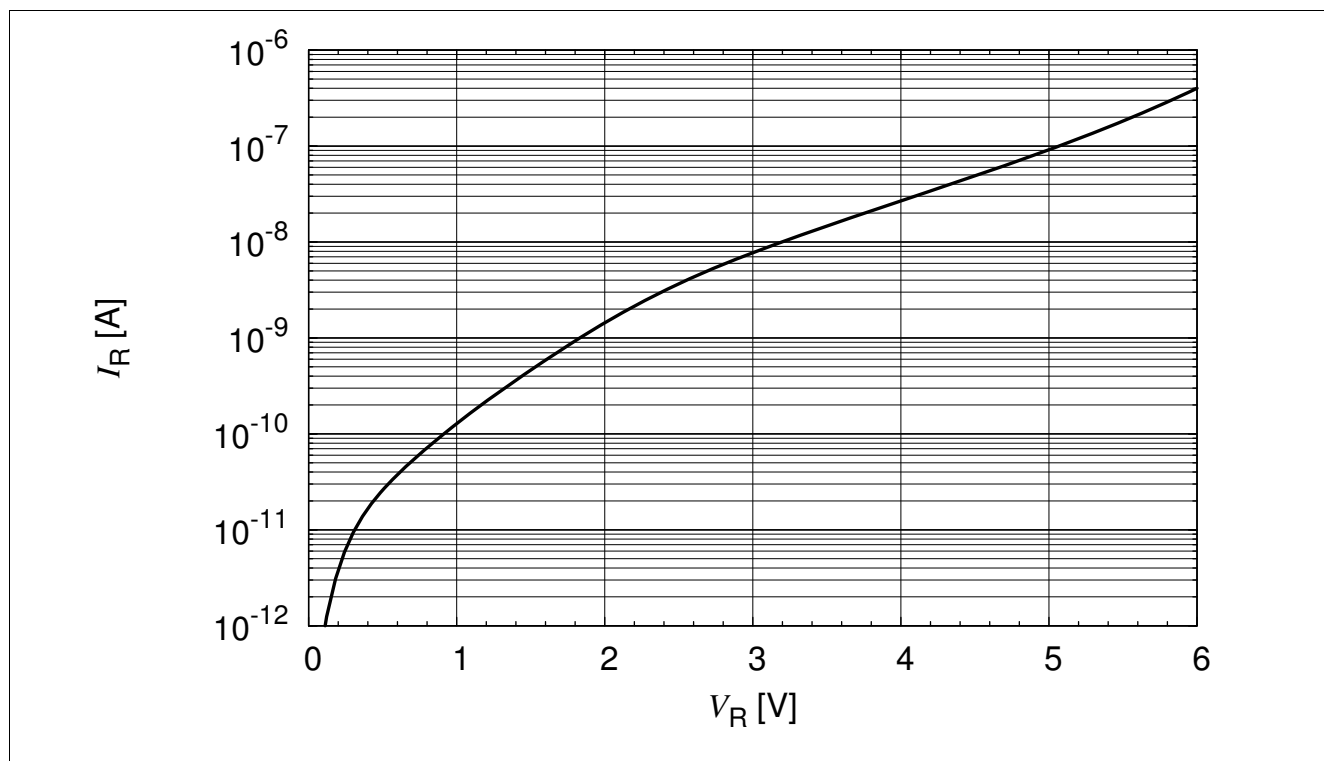
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Line capacitance	C_L	–	17	20	pF	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$

Table 3-4 ESD Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Reverse clamping voltage ¹⁾ [2]	V_{CL}	–	18	–	V	$I_{PP} = 16\text{ A}$
		–	26	–	V	$I_{PP} = 30\text{ A}$
Dynamic resistance ¹⁾ [2]	R_{DYN}	–	0.5	–	Ω	

1) Please refer to Application Note AN210. TLP parameter: $Z_0 = 50\text{ }\Omega$, $t_p = 100\text{ ns}$, $t_r = 300\text{ ps}$, averaging window: $t_1 = 30\text{ ns}$ to $t_2 = 60\text{ ns}$, extraction of dynamic resistance using least squares fit of TLP characteristics between $I_{PP1} = 10\text{ A}$ and $I_{PP2} = 40\text{ A}$.

3.2 Typical Characteristics at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified


Figure 3-2 Reverse current: $I_R = f(V_R)$

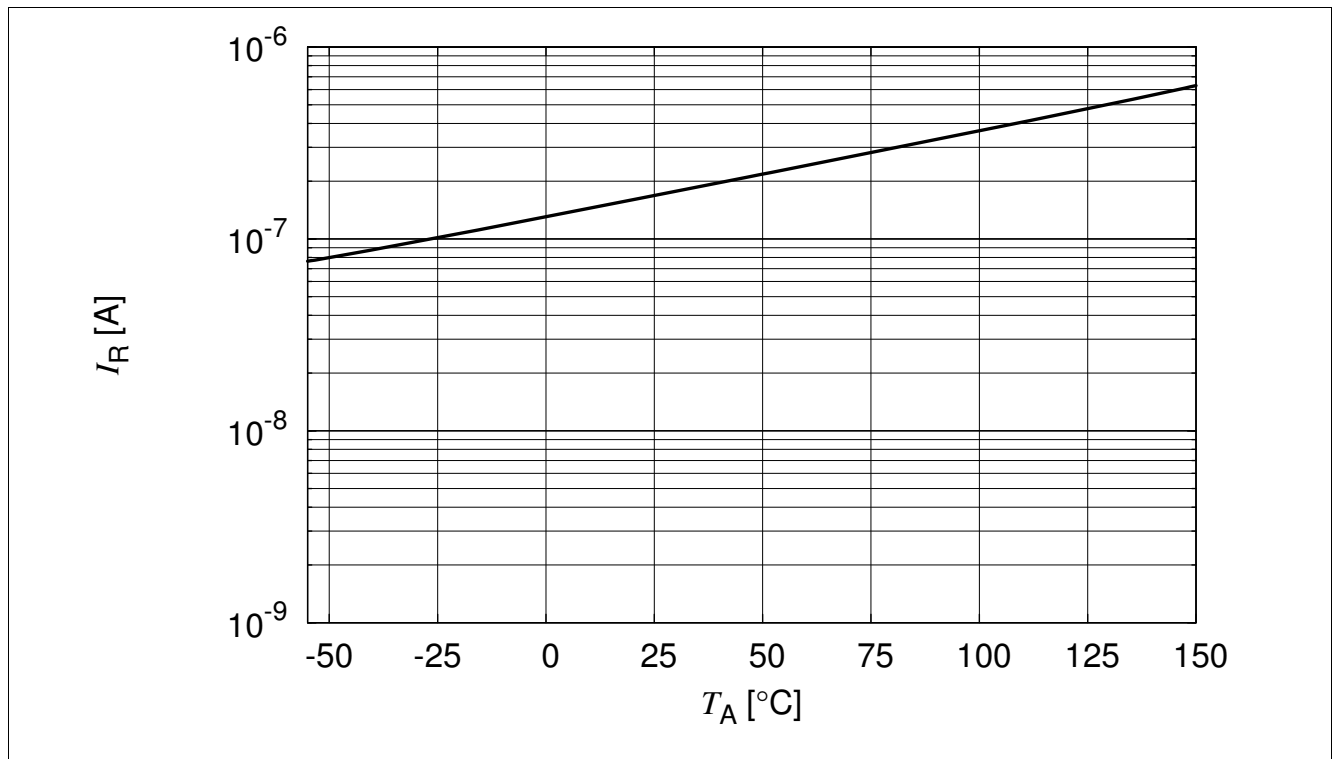


Figure 3-3 Reverse current: $I_R = f(T_A)$, $V_R = 5.3$ V

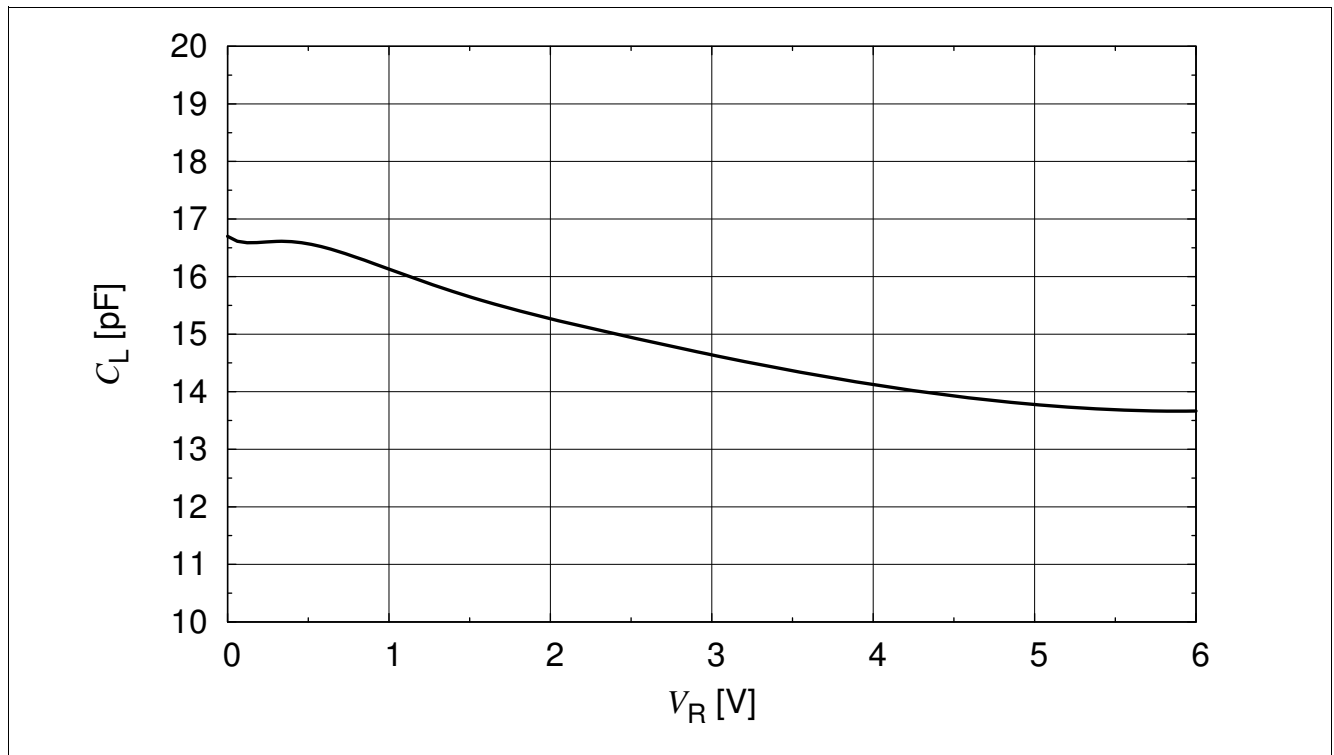


Figure 3-4 Line capacitance: $C_L = f(V_R)$, $f = 1$ MHz

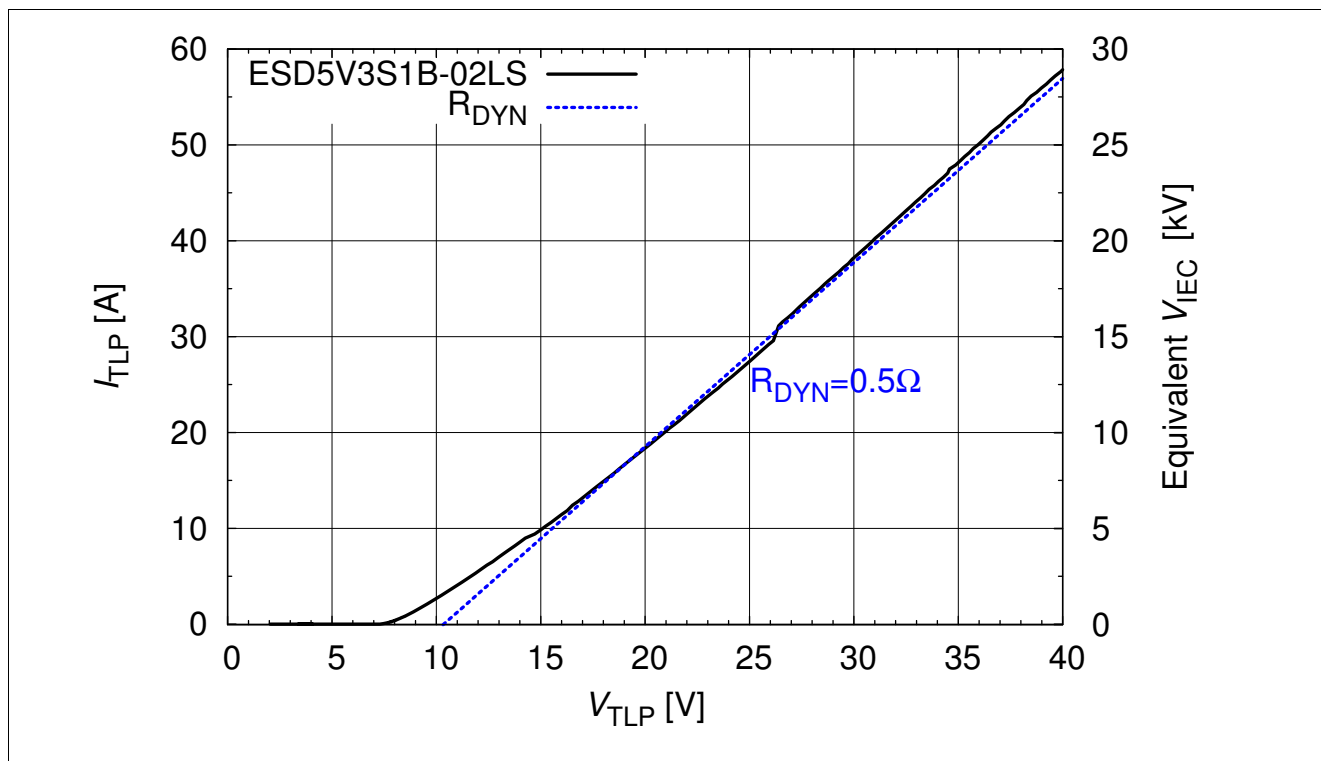


Figure 3-5 Clamping voltage (TLP): $I_{TLP} = f(V_{TLP})$ [1]

4 Application Information

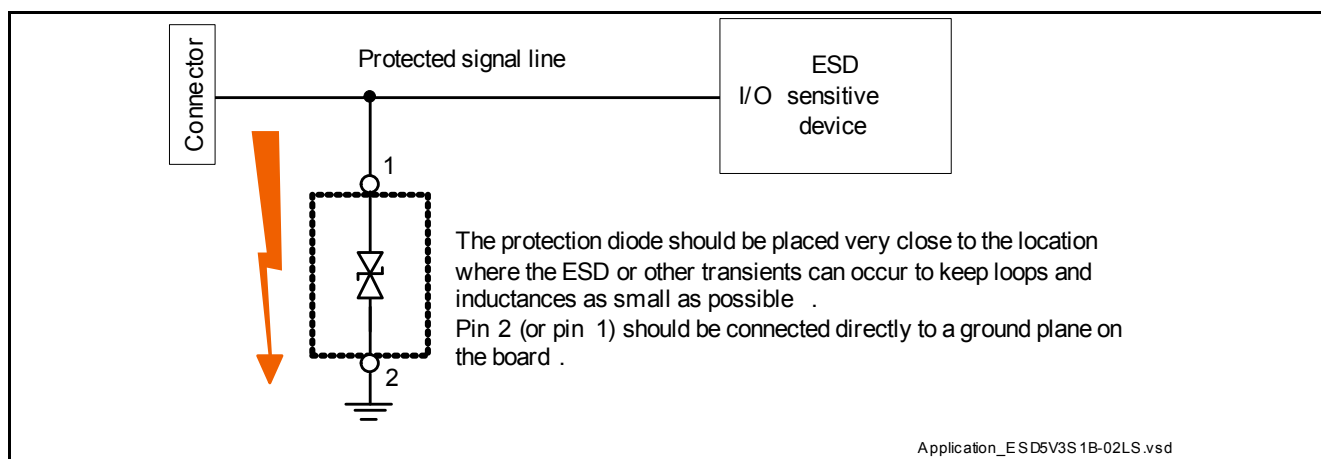


Figure 4-1 Single line, bi-directional ESD / Transient protection

5 Ordering Information Scheme (Examples)

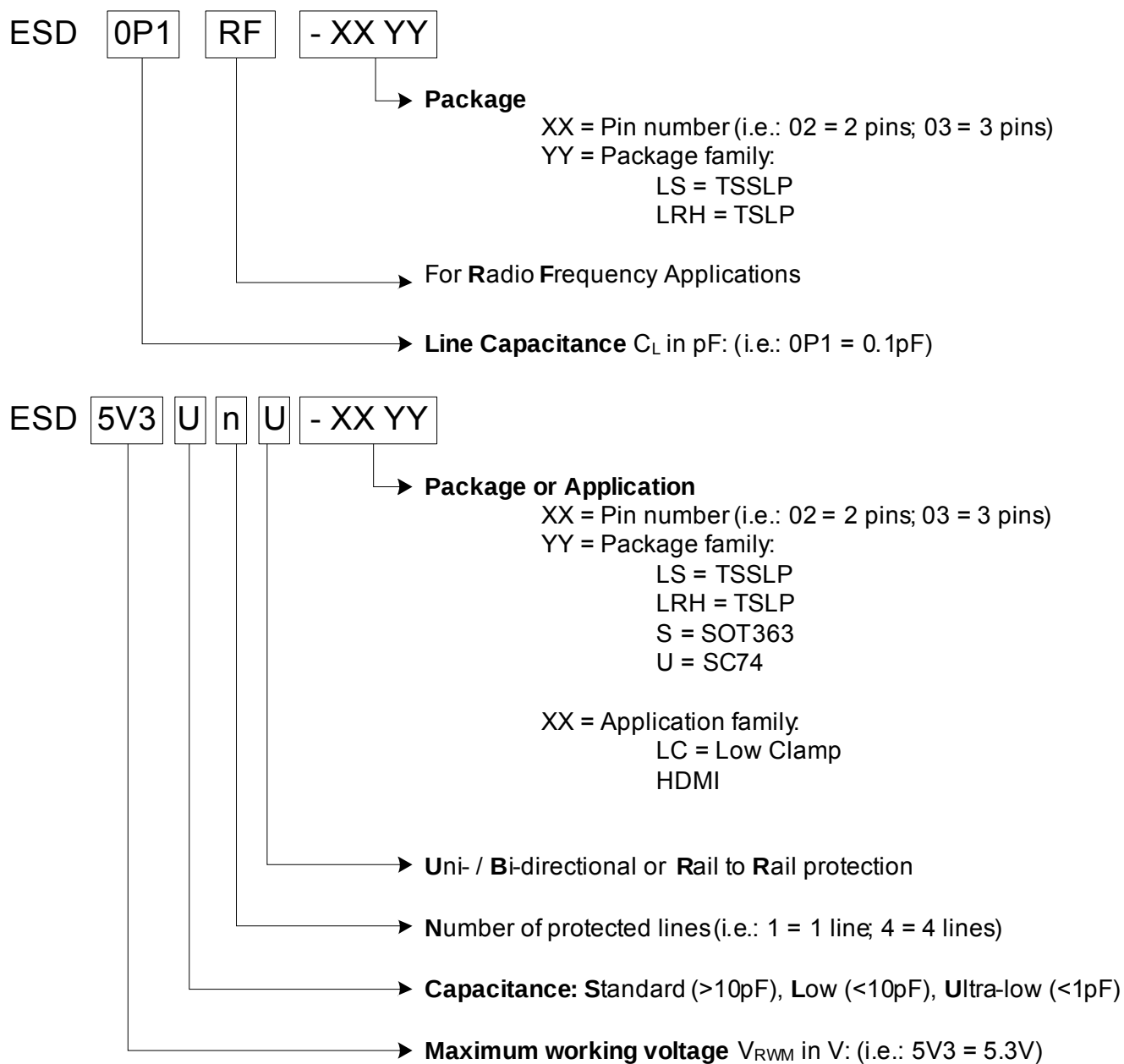


Figure 5-1 Ordering information scheme

6 Package Information

6.1 PG-TSSLP-2-1 (mm) [2]

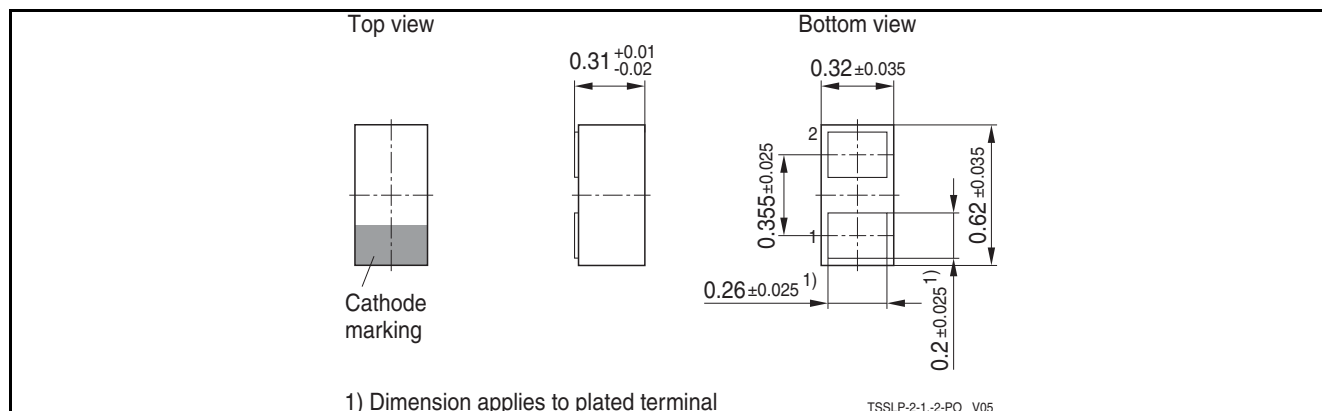


Figure 6-1 PG-TSSLP-2-1: Package overview

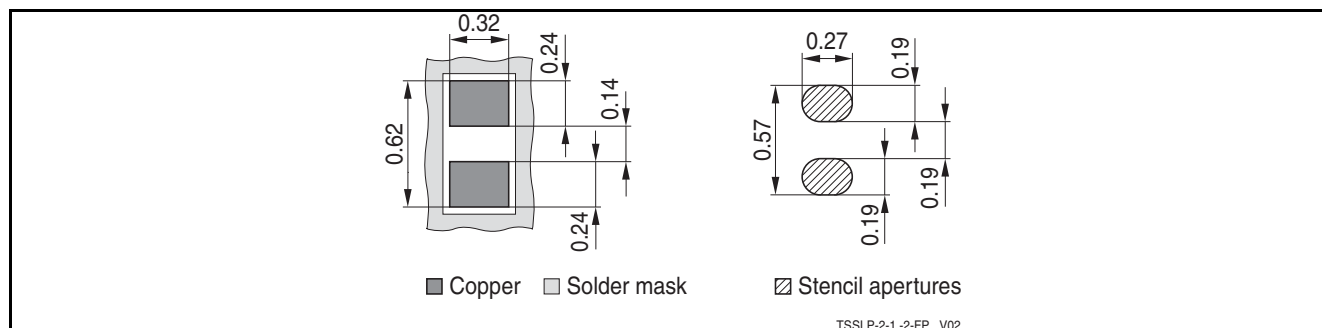


Figure 6-2 PG-TSSLP-2-1: Footprint

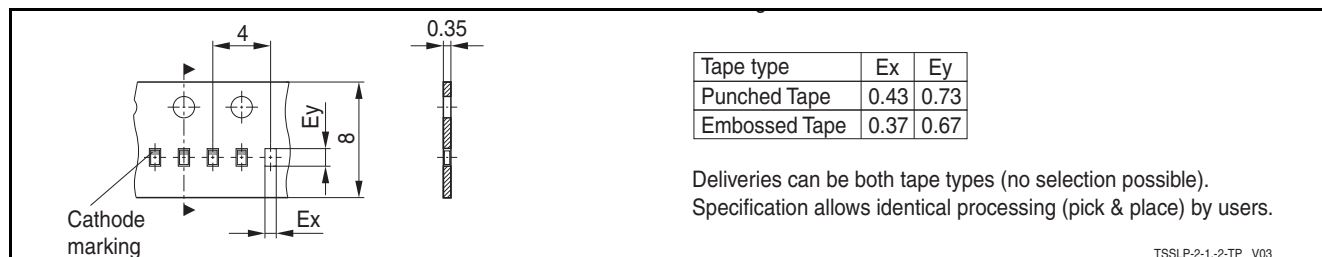


Figure 6-3 PG-TSSLP-2-1: Packing

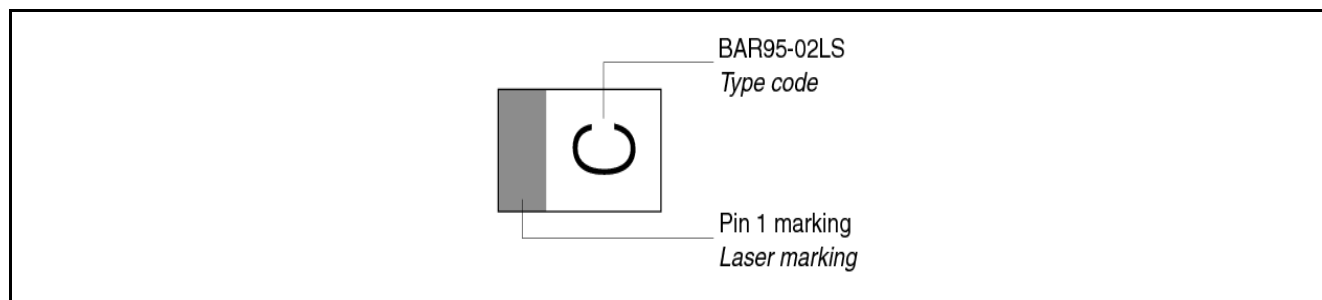


Figure 6-4 PG-TSSLP-2-1: Marking (example)

References

- [1] Infineon AG - **Application Note AN210**: Effective ESD Protection design at System Level Using VF-TLP Characterization Methodology
- [2] Infineon AG - Recommendations for PCB Assembly of Infineon TSLP and TSSLP Packages

Terminology

C_L	Line capacitance
DSC	Digital Still Camera
DVD	Digital Versatile Disc
EFT	Electrical Fast Transient
ESD	Electrostatic Discharge
I_{PP}	Peak pulse current
I_R	Reverse current
LCD	Liquid Crystal Display
MP3	Audio player device based on MPEG Audio Layer III
P_{PK}	Peak pulse power
R_{DYN}	Dynamic resistance
RoHs	Restriction of Hazardous Substance directive
STB	Set-Top-Box
T_A	Ambient temperature
T_{OP}	Operation temperature
t_p	Pulse duration
T_{stg}	Storage temperature
V_{BR}	Breakdown voltage
V_{CL}	Reverse clamping voltage
V_{ESD}	Electrostatic discharge voltage
V_R	Reverse voltage
V_{RWM}	Reverse working voltage maximum

Predefined Names

Name	Initial Cross-Reference
X-GOLD	X-GOLD
XMM	XMM

Definition of “Predefined Names”

Frequently used expressions, such as component names, file names, tools releases, version numbers, proprietary variables and software links, can be used in a similar way as user variables. However, they must be listed in a special table and **not** in the standard file “Variables”.

Correct Usage

Steps:

1. Insert all expressions into the left column of the above table.
2. Insert an initial Cross-Reference into the right column of the same row. The initial Cross-Reference is necessary to ensure that a single ID is used in all your documents using the “Predefined_Names.fm” file (Example: **X-GOLD** has the unique ID = CHDGHJGH).
3. Insert a Cross-Reference (Element “CrossReference”) into your document to the Element Identifier of the “Predefined_Names.fm” file. Set the output format of the Cross-Reference to “Variable” (example: X-GOLD).

Notes

1. All documents in a project (such as XMM) and within a book should use the same file “Predefined Names”. This allows copying content between different documents. For this reason, local versions of “Predefined Names” must not be produced.
2. New definitions must be inserted in a new row. Never change existing definitions, as they might be used in other documents.
3. This file does not need to be included in your book, but it must be in the fm sub-folder of your document.
4. You can sort the above table with FrameMaker only if the initial cross-reference in the right column has been properly inserted. Otherwise, the table may only be sorted by hand, as the cross-references to your document would get lost.

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